

Application No. 09/844,251
Filed: April 27, 2001
TC Art Unit: 2832
Confirmation No.: 8919

AMENDMENT TO THE CLAIMS

1 - 11. (Canceled)

12. (Currently amended) A process for preparing a contact on a microswitch, the process reducing a resistance of the microswitch and maintaining a low resistance of the microswitch for many cycles, comprising:

a. forming the microswitch contact with a predetermined material;

b. temporarily exposing the microswitch contact to a fluid to lower a contact resistance, The process of claim 1 wherein the fluid comprises materials selected from the group consisting of oxygen, carbon tetrafluoride, sulfur hexafluoride or other fluorine-containing gases, argon and mixtures thereof.

13. (Currently amended) The process of claim 12 wherein the ~~material~~ fluid is a gaseous plasma.

14. (Previously presented) The process of claim 13 wherein the plasma is Inductively Coupled Plasma.

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15. (Previously presented) A process for preparing a contact on a microswitch wherein the contact formation includes Ru, comprising temporarily exposing the contact to an oxygen plasma to reduce contact resistance.

16 - 19. (Canceled)

20. (Currently amended) A semiconductor package having a semiconductor die connected to external pins, the die including an active area;

a microswitch formed on a surface of the die, wherein the a microswitch contact is formed with a process for reducing a resistance of the microswitch and maintaining a low resistance of the microswitch for many cycles, comprising:

a. forming the microswitch contact with a predetermined material;

b. temporarily exposing the microswitch contact to a fluid to lower a contact resistance according to the process of claim 1.